

## CORRECTION

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## Correction: Surface organic ligand-passivated quantum dots: toward high-performance light-emitting diodes with long lifetimes

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Correction for 'Surface organic ligand-passivated quantum dots: toward high-performance light-emitting diodes with long lifetimes' by Lishuang Wang et al., *J. Mater. Chem. C*, 2021, 9, 2483–2490, DOI: 10.1039/D0TC05391K.

The Synthesis method of the QDs in the Supplementary Information is incorrect. The QDs were not synthesized by the authors and the QDs used in this work were purchased from Mesolight Inc., the commodity IDs of the QDs are 20200914-2 and 20200914-4 for the DDT-QDs and OT-QDs, respectively.

Mesolight Inc. decided to partly provide their synthesis method:

Synthesis method of QDs:

A mixture of CdO (1 mmol), Zn(Ac)<sub>2</sub> (20 mmol), oleic acid (50 mmol) and 1-octadecene (150 mmol) was loaded into a 250 mL three-necked flask and heated to 310 °C. A certain amount of Se precursor (Se-TOP, 1.2–1.4 mmol) was added and the reactions were kept at 310 °C for 30 min. The reaction mixture was then kept at 240 °C, 15 mmol of 1-dodecanethiol and 10 mmol of the as-prepared stock solution for the Zn precursor and another 5 mL of the as-prepared stock solution for the S precursor were injected into the flask. The reaction was continued for more than 30 min. Finally, the flask was cooled to room temperature. By comparison, the QDs capped with OT ligands were synthesized by the same procedure during the growth of a ZnS outer shell.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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